

IN THE CLAIMS:

1. (Once Amended) A method of forming a contact for a semiconductor device, comprising the steps of:

forming a first interlayer dielectric layer on a silicon substrate;

forming a conductive material pattern on a portion of the first interlayer dielectric layer;

forming a second interlayer dielectric layer over the first interlayer dielectric layer and over the conductive material pattern;

forming first and second contact holes by selectively removing the second and the first interlayer dielectric layers so as to respectively expose a portion of the conductive material pattern and a portion of the silicon substrate;

forming a glue layer on the first and the second interlayer dielectric layers including over the first and the second contact holes, the glue layer including a CVD TiN layer;

treating plasma on the glue layer using N_2 or H_2 , alone or in combination, during the step of forming the glue layer; and

filling the first and the second contact holes with a tungsten layer by forming the tungsten layer on the glue layer.

5. (Once Amended) The method of claim 4, wherein a plasma treatment is further performed after the deposition of the CVD TiN layer while using N_2 and H_2 gas either together or alone.

10. (Once Amended) A method of forming a contact for a semiconductor device, comprising the steps of:

forming a first interlayer dielectric layer on a silicon substrate;

forming a conductive material pattern on a portion of the first interlayer dielectric layer, wherein the conductive material pattern has a lower etch rate than the first interlayer dielectric layer;

forming a second interlayer dielectric layer over the first interlayer dielectric layer and over the conductive material pattern;

selectively and sequentially removing the second and the first interlayer dielectric layers so as to form first and second contact holes, wherein the second

contact hole has a depth greater than the first contact hole, wherein the first contact hole exposes a portion of the conductive material pattern, and wherein the second contact hole exposes a portion of the silicon substrate;

forming at least one CVD TiN layer on the first and the second interlayer dielectric layers including over the first and the second contact holes;

treating plasma on the glue layer using N_2 or H_2 , alone or in combination, during the step of forming the glue layer; and

forming a tungsten layer on the CVD TiN layer so as to fill the first and the second contact holes.

14. (Once Amended) The method of claim 13, wherein a plasma treatment is further performed after the deposition of the CVD TiN layer while using N_2 and H_2 gas either together or alone.